

N-Channel Power MOSFET

900V, 9.0A, 1.4Ω

FEATURES

- 100% Avalanche Tested
- G-S ESD Protection Diode Embedded
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

KEY PERFORMANCE PARAMETERS				
PARAMETER	VALUE	UNIT		
V_{DS}	900	V		
R _{DS(on)} (max)	1.4	Ω		
Q_{g}	72	nC		

APPLICATION

- Power Supply
- Lighting



ABSOLUTE MAXIMUM RATINGS (T _A =25°C unless otherwise noted)					
PARAMETER		SYMBOL	TO-220	ITO-220	UNIT
Drain-Source Voltage		V_{DS}	900		V
Gate-Source Voltage		V_{GS}	±30		V
Continuous Drain Current	$T_C = 25^{\circ}C$		9.0		Α
	$T_C = 100$ °C	I _D	5.7		
Pulsed Drain Current (Note 2)		I _{DM}	3	6	Α
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	290	89	W
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	454		mJ
Single Pulsed Avalanche Current (Note 3)		I _{AS}	9		Α
Operating Junction and Storage Temperature Range		T_J,T_STG	- 55 to +150		°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT
Junction to Case Thermal Resistance	R _{eJC}	0.43	1.4	°C/W
Junction to Ambient Thermal Resistance	R _{eJA}	62.5		°C/W

Notes: R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{eJA} is guaranteed by design while R_{eCA} is determined by the user's board design. R_{eJA} shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	900			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, \ I_D = 250 \mu A$	$V_{GS(TH)}$	2.0		4.0	V
Gate Body Leakage	$V_{GS} = \pm 30 V$, $V_{DS} = 0 V$	I _{GSS}			±100	μΑ
Zero Gate Voltage Drain Current	$V_{DS} = 900V, V_{GS} = 0V$	I _{DSS}			10	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 4.5A$	R _{DS(on)}		1.13	1.4	Ω
Dynamic (Note 5)						
Total Gate Charge	7001/ 1 0 0 4	Q_g		72	<u></u>	nC
Gate-Source Charge	$V_{DS} = 720V, I_{D} = 9.0A,$	Q_gs		+		
Gate-Drain Charge	$V_{GS} = 10V$	Q_{gd}		31		
Input Capacitance		C _{iss}		2470		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	Coss		192		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss})	27		
Switching (Note 6)						
Turn-On Delay Time		$t_{d(on)}$		52		
Turn-On Rise Time	$V_{DD} = 450V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 9.0A, V_{GS} = 10V,$	t _r		97		
Turn-Off Delay Time		t _{d(off)}		212		ns
Turn-Off Fall Time	$I_D = 9.0A$, $V_{GS} = 10V$,	t _f		159		
Source-Drain Diode (Note 4)						
Forward On Voltage	I _S = 9.0A, V _{GS} = 0V	V_{SD}			1.5	V
Reverse Recovery Time	$V_{GS} = 0V$, $I_{S} = 9A$,	t _{fr}		570		ns
Reverse Recovery Charge	dl _F /dt = 100A/us	Q _{fr}		6.6		μC

Notes:

- Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 10.6mH, $I_{AS} = 9A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$ 100% Eas Test Condition: L = 10.6mH, $I_{AS} = 4.5A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$
- 4. Pulse test: PW ≤ 300µs, duty cycle ≤ 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

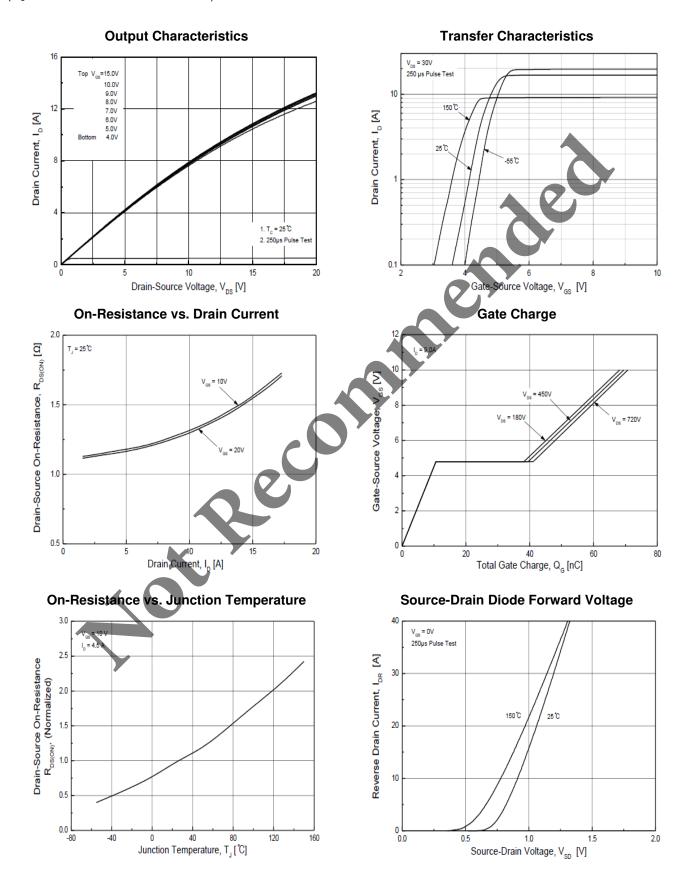
PART NO.	PACKAGE	PACKING
TSM9N90ECZ C0G	TO-220	50pcs / Tube
TSM9N90ECI C0G	ITO-220	50pcs / Tube





CHARACTERISTICS CURVES

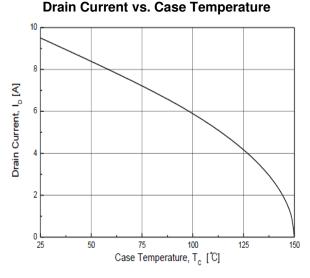
(T_C = 25°C unless otherwise noted)



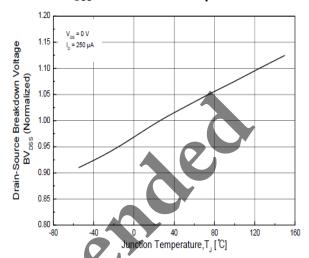


CHARACTERISTICS CURVES

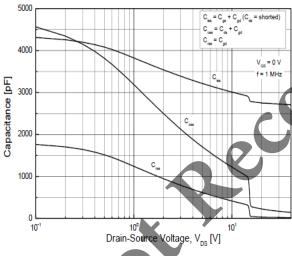
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

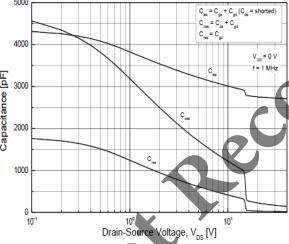


BV_{DSS} vs. Junction Temperature

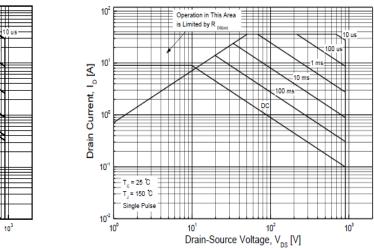


Capacitance vs. Drain-Source Voltage

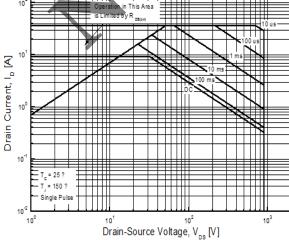




Maximum Safe Operating Area (ITO-220)



Maximum Safe Operating Area (TO-220)

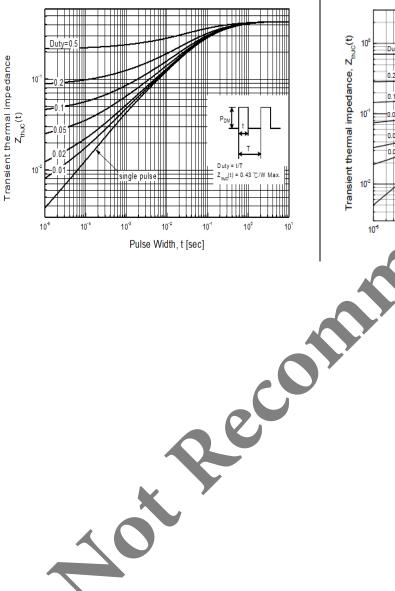




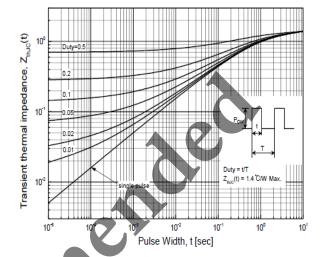
ELECTRICAL CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-220)

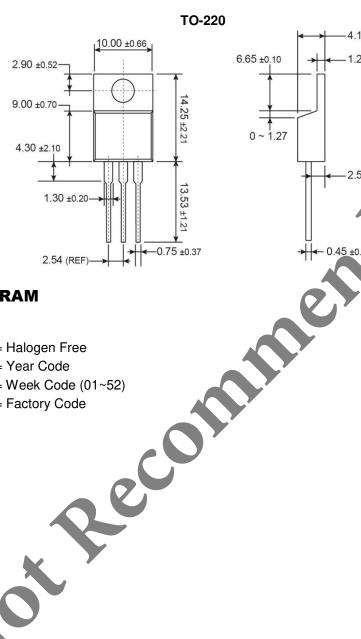


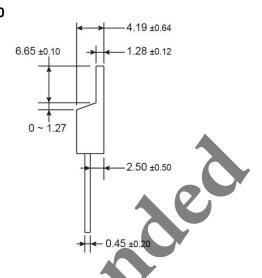
Normalized Thermal Transient Impedance, Junction-to-Ambient (ITO-220)



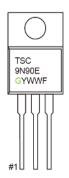


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





MARKING DIAGRAM



= Halogen Free

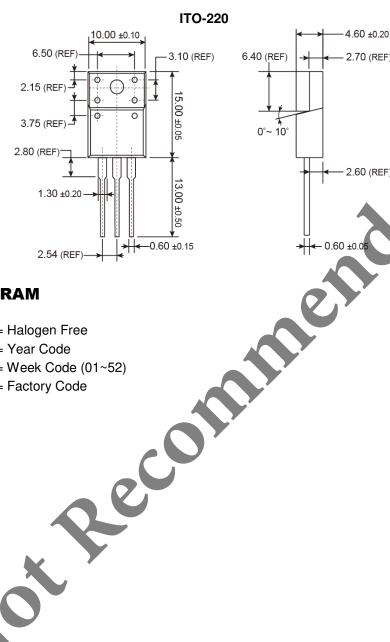
Y = Year Code

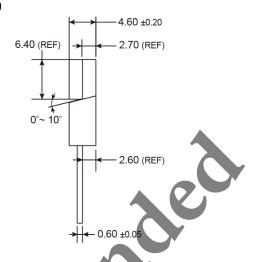
WW = Week Code $(01 \sim 52)$

= Factory Code

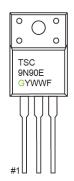


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





MARKING DIAGRAM



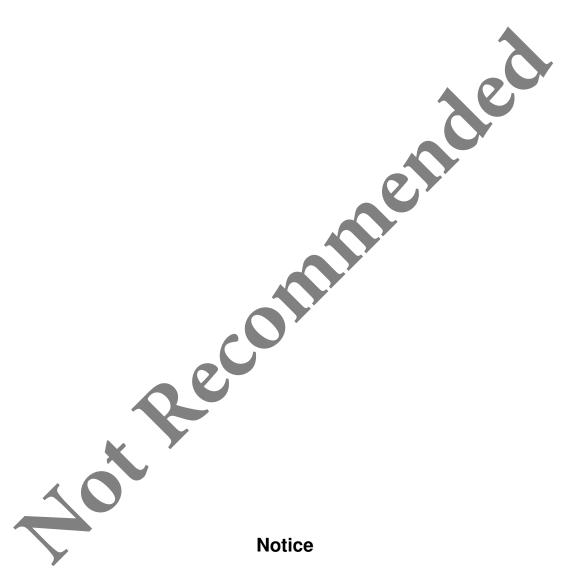
= Halogen Free

= Year Code

WW = Week Code (01~52)

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